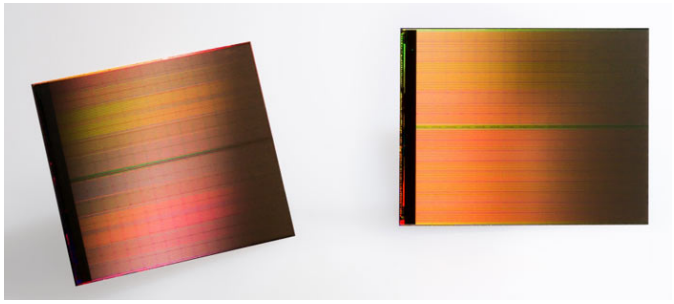
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Intel and Micron create a new memory category, the first since the 1989 introduction of NAND flash-- 3D XPoint, a kind of memory the companies say is up to 1000x faster than NAND and 10x denser than conventional memory.



The result of over a decade of R&D, 3D XPoint memory features a transistor-less cross point architecture built in a "3D checkerboard." Memory cells sit at the intersection of word lines and bit lines, allowing the individual addressing of cells. The result is data written and read in small sizes, leading to faster and more efficient read/write processes.

"For decades, the industry has searched for ways to reduce the lag time between the processor and data to allow much faster analysis," Intel says. "This new class of non-volatile memory achieves this goal and brings game-changing performance to memory and storage solutions."

The technology should find both enterprise and consumer applications-- the current big data trends demands increasingly dense and faster memory, while consumers always appreciate enhanced PC experiences.

Currently Intel and Micron are developing individual 3D Xpoint products, and sampling with select customers should start later during the year.

Go Intel and Micron Produce Breakthrough Memory Technology